

Description

The STD35NF06 uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

 $V_{DS} = 60V I_{D} = 50 A$

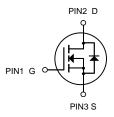
 $R_{DS(ON)}$ < 17m Ω @ V_{GS} =10V

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
STD35NF06	TO-252-2L	HXY MOSFET	2500

Absolute Maximum Ratings (T_C=25°Cunless otherwise noted)

Symbol	Parameter	Rating	Units	
V _D s	Drain-Source Voltage	60	V	
Vgs	Gate-Source Voltage	±20	V	
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	50	А	
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	38	А	
Ідм	Pulsed Drain Current ²	180		
EAS	Single Pulse Avalanche Energy ³	280	mJ	
las	Avalanche Current	28	А	
P _D @T _C =25°C	Total Power Dissipation ⁴	87.7	W	
Тѕтс	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150 °C		
R _θ JA	Thermal Resistance Junction-Ambient ¹	62 °C/M		

Electrical Characteristics (T_C=25 [°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·		•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)			•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\mu A$	1.0	1.5	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =30A	-	13	17	mΩ
Forward Transconductance	G FS	V _{DS} =5V,I _D =30A	30	-	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C _{lss}		-	2498	-	PF
Output Capacitance	Coss	$V_{DS}=25V, V_{GS}=0V,$	-	185	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	80	-	PF
Switching Characteristics (Note 4)			II	Į.		•
Turn-on Delay Time	t _{d(on)}		-	12	-	nS
Turn-on Rise Time	t _r	V_{DD} =30V, I_D =2A, R_L =1 Ω	-	5.2	-	nS
Turn-Off Delay Time	$t_{d(off)}$	V_{GS} =10V, R_{GEN} =3 Ω	-	38	-	nS
Turn-Off Fall Time	t _f		-	27	-	nS
Total Gate Charge	Qg	V 00V/1 00A	-	36	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =30V,I _D =30A,	-	9.9	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	6.6	-	nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =30A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	58	А
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF =30A	-	35		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	47		nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

- **1.** Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- **5.** E_{AS} condition: Tj=25 $^{\circ}$ C,V_{DD}=30V,V_G=10V,L=0.5mH,Rg=25 Ω

Typical Electrical and Thermal Characteristics (Curves)

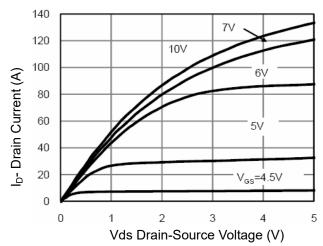


Figure 1 Output Characteristics

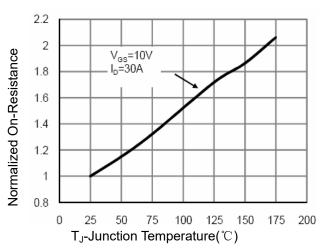


Figure 4 Rdson-JunctionTemperature

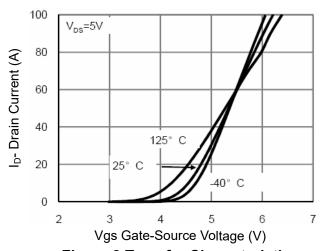


Figure 2 Transfer Characteristics

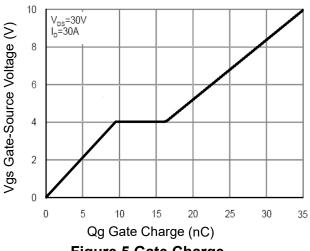


Figure 5 Gate Charge

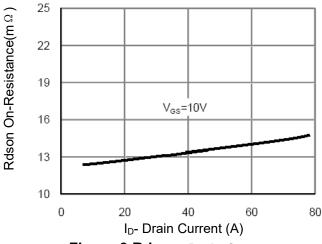


Figure 3 Rdson- Drain Current

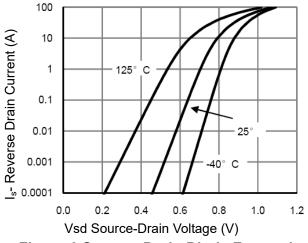
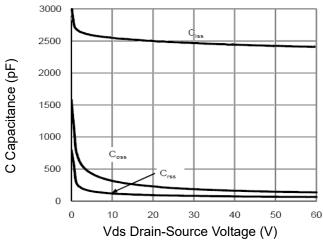


Figure 6 Source- Drain Diode Forward

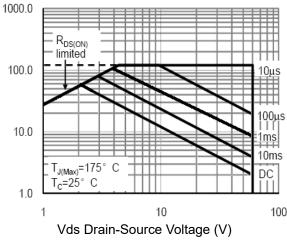




120 90 Power Dissipation (W) 60 30 0 75 100 0 175 T_J -Junction Temperature($^{\circ}$ C)

Figure 7 Capacitance vs Vds

Figure 9 Power De-rating



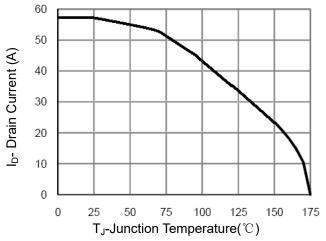
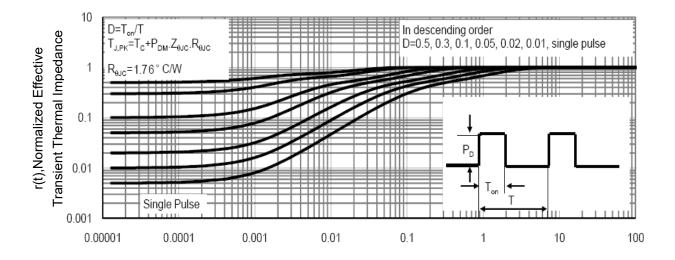


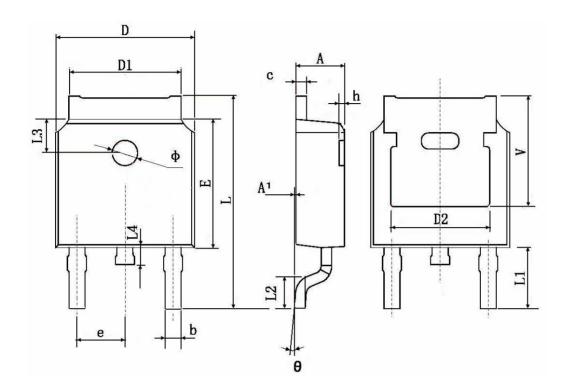
Figure 8 Safe Operation Area

Figure 10 ID Current- JunctionTemperature





TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	0.483 TYP.		0.190 TYP.		
Е	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350 TYP.		0.211 TYP.		



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